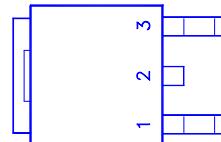
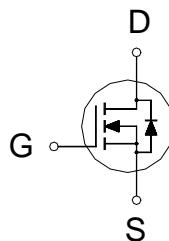


NIKO-SEM
**N-Channel Logic Level Enhancement
Mode Field Effect Transistor**
P70N02LD
TO-252 (DPAK)
PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
25	7mΩ	60A



1. GATE
-
2. DRAIN
-
3. SOURCE

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	60	A
	$T_C = 100^\circ\text{C}$		40	
Pulsed Drain Current ¹		I_{DM}	150	
Avalanche Current		I_{AR}	60	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	140	mJ
Repetitive Avalanche Energy ²	$L = 0.05\text{mH}$	E_{AR}	5.6	
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	60	W
	$T_C = 100^\circ\text{C}$		32.75	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C
Lead Temperature ($\frac{1}{16}$ " from case for 10 sec.)		T_L	275	

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		2.5	
Junction-to-Ambient	$R_{\theta JA}$		65	°C / W
Case-to-Heatsink	$R_{\theta CS}$	0.7		

¹Pulse width limited by maximum junction temperature.²Duty cycle ≤ 1%**ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$, Unless Otherwise Noted)**

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	25			V
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1	1.5	3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			± 250	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}$			25	μA
		$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}, T_J = 125^\circ\text{C}$			250	

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On-State Drain Current ¹	$I_{D(ON)}$	$V_{DS} = 10V, V_{GS} = 10V$	60			A
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 30A$		7	9	$m\Omega$
		$V_{GS} = 7V, I_D = 24A$		8	10	
Forward Transconductance ¹	g_f	$V_{DS} = 15V, I_D = 30A$		16		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$		2700		pF
Output Capacitance	C_{oss}			500		
Reverse Transfer Capacitance	C_{rss}			200		
Total Gate Charge ²	Q_g	$V_{DS} = 0.5V_{(BR)DSS}, V_{GS} = 10V, I_D = 30A$		25		nC
Gate-Source Charge ²	Q_{gs}			7		
Gate-Drain Charge ²	Q_{gd}			11		
Turn-On Delay Time ²	$t_{d(on)}$	$V_{DS} = 15V, R_L = 1\Omega$ $I_D \approx 30A, V_{GS} = 10V, R_{GS} = 2.5\Omega$		7		nS
Rise Time ²	t_r			7		
Turn-Off Delay Time ²	$t_{d(off)}$			24		
Fall Time ²	t_f			6		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_C = 25^\circ C$)						
Continuous Current	I_S				60	A
Pulsed Current ³	I_{SM}				150	
Forward Voltage ¹	V_{SD}	$I_F = I_S, V_{GS} = 0V$			1.3	V
Reverse Recovery Time	t_{rr}	$I_F = I_S, dI_F/dt = 100A / \mu S$		37		nS
Peak Reverse Recovery Current	$I_{RM(REC)}$			200		A
Reverse Recovery Charge	Q_{rr}			0.043		μC

¹Pulse test : Pulse Width $\leq 300 \mu sec$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

³Pulse width limited by maximum junction temperature.

REMARK: THE PRODUCT MARKED WITH "P70N02LD", DATE CODE or LOT #

NIKO-SEM**N-Channel Logic Level Enhancement
Mode Field Effect Transistor****P70N02LD
TO-252 (DPAK)****TO-252 (DPAK) MECHANICAL DATA**

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	9.35		10.1	H		0.8	
B	2.2		2.4	I	6.4		6.6
C	0.48		0.6	J	5.2		5.4
D	0.89		1.5	K	0.6		1
E	0.45		0.6	L	0.64		0.9
F	0.03		0.23	M	4.4		4.6
G	6		6.2	N			

